

An Accurate Approach for Calculating the Efficiency of a Synchronous Buck Converter Using the MOSFET Plateau Voltage

Xing He, Daniel Li, Vincent Zhang

ABSTRACT

This application note shows how to calculate the power loss for a synchronous buck converter. It discusses the theory calculation for switch losses, inductor losses, input and output capacitor ESR losses, and other losses, as well as their effect to the efficiency of a synchronous buck converter. Additionally, this article introduces a method to estimate the MOSFET plateau (V_{pl}) voltage for different drain to source currents. With the more accurate MOSFET plateau voltage, highly-accurate efficiency calculations can be made.

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1 Overview

TI buck switching solutions include power modules, converters (regulators) and controllers. With integrated FETs and inductor, power modules simplify your power supply design process and get you to market faster. With an integrated FET or FETs and external inductor, converters provide a good balance of integration and flexibility. Controllers with external FETs and inductors provide the most design flexibility for high-power applications. This flexibility allows customers to choose FETs and diode maximizing efficiency at a particular load level. Buck switching regulators are also divided into synchronous buck and non-synchronous. The difference is that synchronous regulators integrate low side switch to replace the external diode in non-synchronous, which helps improve efficiency.

Customers will estimate the efficiency of the buck converter when they choose a controller IC. For either space constrained applications or higher power designs where ambient temperature are high, accurately efficiency calculations are necessary. Several losses in buck converter must be calculated to estimate the efficiency and losses.

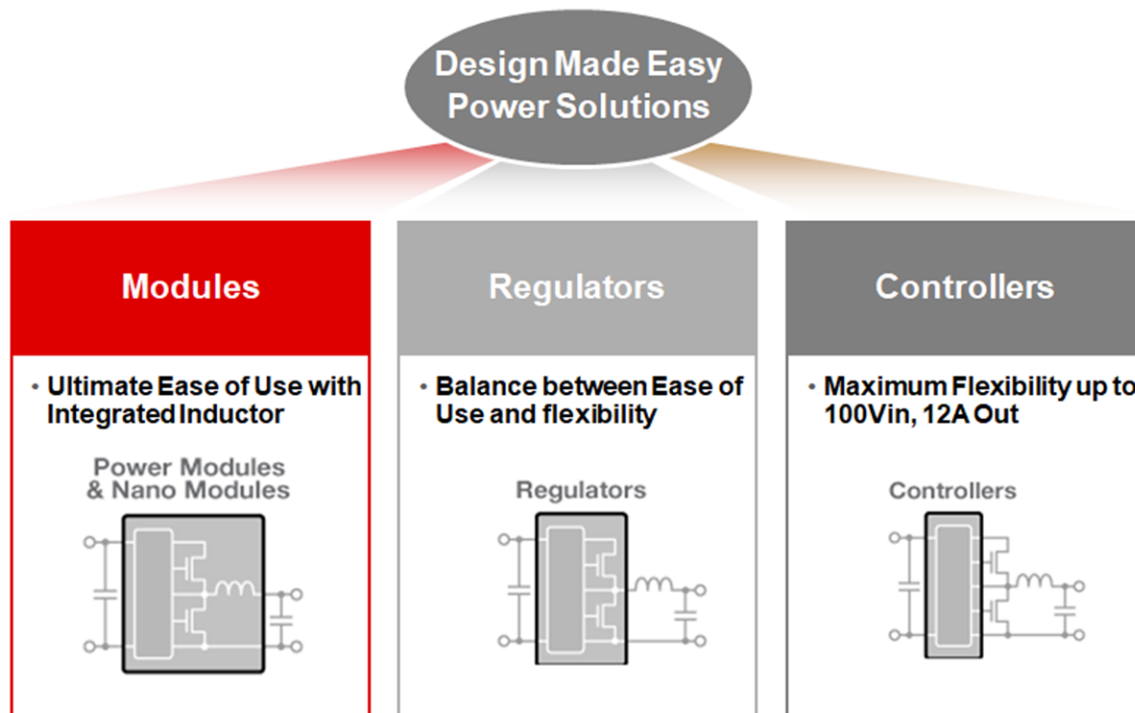


Figure 1. TI Buck Switching Solutions

2 Power Losses Calculation for Synchronous Buck Converter

Figure 2 shows the power losses of synchronous buck converter, including the switching losses, the inductor losses, the capacitor losses and other losses. The efficiency calculation is shown in Equation 1 and Equation 2. This section shows how to calculate these power losses.

$$P_{total_loss} = P_{switches} + P_{inductor} + P_{capacitors} + P_{other} \tag{1}$$

$$\eta = \frac{V_o I_o}{V_o I_o + P_{total_loss}} \times 100\% \tag{2}$$

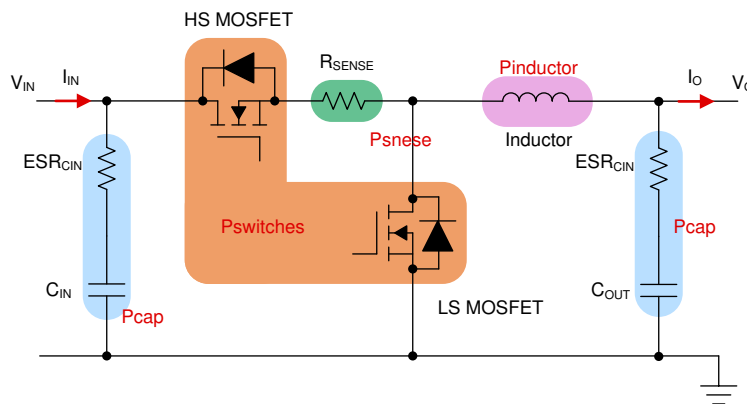


Figure 2. Power Losses of Synchronous Buck Converter

2.1 Switching Losses Calculation

There are two MOSFETs in synchronous buck converter, the High side (HS) MOSFET and the Low side (LS) MOSFET. The MOSFETs losses are composed of several parts: switching loss, conduction loss, gate drive loss, output capacitance loss, and LS MOSFET body-diode loss. These losses are analyzed in the following sections.

2.1.1 Switching Loss Calculation

Figure 3 illustrates the MOSFETs turn on and turn off transition. It can be divided into five parts:

Time t_0 : the MOSFET turns off, V_{GS} is zero;

Time t_1 : V_{GS} reaches V_{TH} ;

Time t_2 : V_{GS} reaches V_{PL} , MOSFET begins turn on, I_{DS} is increased from zero to I_O ;

Time t_3 : V_{GS} stays in V_{PL} , MOSFET keeps turning on, I_{DS} is I_O , V_{DS} is reduced from V_{IN} to zero;

Time t_4 : V_{GS} keeps increased, MOSFET fully turns on;

During the transition (Time t_2 and Time t_3), the I_{DS} and V_{DS} are not zero, so the switching loss is caused when MOSFET turns on and turns off. Equation 3 shows the switching loss calculation.

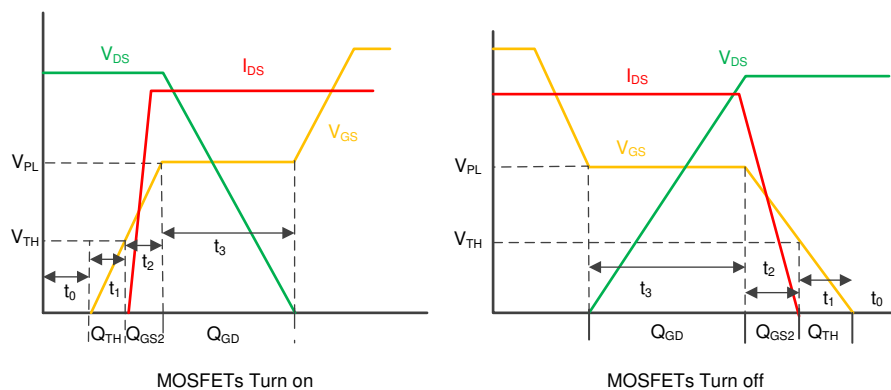


Figure 3. MOSFET Switch Transition

$$P_{\text{switching}} = \frac{V_{in}}{2} \left(I_o - \frac{\Delta i_{Lpp}}{2} \right) \times f_{sw} \times t_r + \frac{V_{in}}{2} \left(I_o + \frac{\Delta i_{Lpp}}{2} \right) \times f_{sw} \times t_{off} \quad (3)$$

Δi_{Lpp} is the ripple current in the inductor. t_r is the switching time when MOSFET turns on, t_{off} is switching time when MOSFET turns off. f_{sw} is the switching frequency.

$$\Delta i_{Lpp} = \frac{V_{in} - V_o}{L} \frac{V_o}{V_{in}} \frac{1}{f_{sw}} \quad (4)$$

$$t_r = t_1 + t_2 = \left(\frac{Q_{gs2}}{V_{dr} - 0.5 \times (V_{pl} + V_{gs(th)})} + \frac{Q_{gd}}{V_{dr} - V_{pl}} \right) (R_g + R_{drive}) \quad (5)$$

$$t_{off} = t_3 + t_4 = \left(\frac{Q_{gs2}}{V_{dr} - 0.5 \times (V_{pl} + V_{gs(th)})} + \frac{Q_{gd}}{V_{pl}} \right) \times (R_g + R_{drive}) \quad (6)$$

Use Equation 3 to calculate the HS MOSFET switching loss in a synchronous buck converter. Since the LS MOSFET can achieve Zero Voltage Switching (ZVS) turn on and Zero Current Switching (ZCS) turn off, the switching loss of LS MOSFET can be neglected.

2.1.2 Conduction Loss Calculation

The conduction loss is determined by the on-resistances of the MOSFETs and the transistor RMS current. Considering the temperature dependency of on-resistances δ and the inductor ripple current, specifically, the conduction loss for HS FET and the LS FET can be calculated by using Equation 7 and Equation 8, respectively:

$$P_{HS_conduction} = R_{HS_ds_on} (1 + \delta) \times I_o^2 \times D \times \left(1 + \frac{1}{12} \left(\frac{\Delta i_{Lpp}}{I_o} \right)^2 \right) \quad (7)$$

$$P_{LS_conduction} = R_{LS_ds_on} (1 + \delta) \times I_o^2 \times (1 - D) \times \left(1 + \frac{1}{12} \left(\frac{\Delta i_{Lpp}}{I_o} \right)^2 \right) \quad (8)$$

2.1.3 Gate Drive Loss Calculation

The gate drive loss of the MOSFETs is caused by the energy required to charge and discharge the MOSFET gate, as Figure 4 shows. It can be calculated by using Equation 9, Q_g is the total gate charge. The gate drive loss is frequency dependent and also a function of the gate capacitance of the MOSFET. The higher switching frequency, the higher the gate-drive loss is. This contributes to the efficiency reducing as the switching frequency goes up. Normally, larger MOSFETs with lower $R_{DS(on)}$ provide lower conduction loss at the cost of higher gate capacitances, which results in higher gate-drive losses.

$$P_{gate_drive} = Q_g \times V_{drive} \times f_{sw} \quad (9)$$

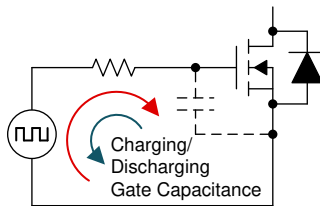


Figure 4. Gate Drive Loss of MOSFET

2.1.4 Other Losses

Output capacitance loss is another part of the MOSFET power losses, which is induced by output capacitance charge/discharge. The C_{oss} loss for HS and LS FETs can be calculated in Equation 10 and Equation 11.

$$P_{HS_Coss} = \frac{1}{2} Q_{oss1} \times V_{in} \times f_{sw} \quad (10)$$

$$P_{LS_Coss} = \frac{1}{2} Q_{oss2} \times V_{in} \times f_{sw} \quad (11)$$

Qoss1 and Qoss2 are the output charge of HS and LS MOSFETs respectively. In a synchronous buck converter, the low-side MOSFET switching loss is negligible as it is switched at zero voltage, current just commutates from the channel to the body diode or vice versa during the transition dead-times. So the body diode loss is another part of loss of LS MOSFET. It is composed of body diode reverse recovery loss and body diode conduction loss, which can be calculated using [Equation 12](#) and [Equation 13](#), respectively.

$$P_{\text{DRR}} = V_{\text{in}} \times Q_{\text{RR}} \times f_s \quad (12)$$

$$P_{\text{dead}} = V_F \left(I_o - \frac{\Delta i_{\text{Lpp}}}{2} \right) \times t_{\text{dr}} \times f_s + V_F \left(I_o + \frac{\Delta i_{\text{Lpp}}}{2} \right) \times t_{\text{df}} \times f_s \quad (13)$$

Qrr is the reverse recovery charge of body diode, V_F is the diode forward voltage and the t_{dr} and t_{df} are the dead times at the turn off and turn on intervals.

2.2 Inductor Losses Calculation

The inductor loss is composed of two parts: winding loss and the core loss. Winding loss of inductor caused by the inductor series resistance ESR_L , it can be calculated by using [Equation 14](#). Core loss is related to core material, operating frequency, output current and current ripple in the inductor, as show in [Equation 15](#).

$$P_{\text{L_winding}} = \text{ESR}_L \times I_{\text{out}}^2 \times \left(1 + \frac{1}{12} \left(\frac{\Delta i_{\text{Lpp}}}{I_o} \right)^2 \right) \quad (14)$$

$$P_{\text{L_core}} = K_1 \times f_s^\alpha \left(K_2 \Delta i_{\text{Lpp}} \right)^\beta \quad (15)$$

K_1 , K_2 , α , β depend on the core material, operating frequency and operating temperature.

2.3 Input and Output Capacitor Losses Calculation

Normally ESR of the input and output capacitors also cause power loss of a buck converter. Usually the ceramic capacitors typically have very small ESR and the electrolytic capacitors typically have larger ESR. The input capacitors and output capacitors loss can be calculated using [Equation 16](#) and [Equation 17](#) respectively.

$$P_{\text{Cin_Loss}} = \text{ESR}_{\text{Cin}} \times I_{\text{out}}^2 \times D \times (1 - D) \quad (16)$$

$$P_{\text{Cout_Loss}} = \text{ESR}_{\text{Cout}} \times \frac{1}{12} \times \Delta i_{\text{Lpp}}^2 \quad (17)$$

2.4 Other Losses

The sense resistor and the control IC also cause power loss in buck converters. Typically their losses are very small so that it will have little influence on efficiency. When the sense resistor is series with the HS MOSFET, the loss caused by sense resistor can be calculated using [Equation 18](#). The control IC loss is calculated using [Equation 19](#) The I_μ is the quiescent current of a control IC.

$$P_{\text{sense}} = R_{\text{sense}} \times I_{\text{out}}^2 \times D \times \left(1 + \frac{1}{12} \Delta i_{\text{Lpp}}^2 \right) \quad (18)$$

$$P_{\text{IC}} = V_{\text{in}} \times I_\mu \quad (19)$$

3 MOSFETs' V_{pl} and $V_{gs(th)}$ Estimation

3.1 Theory for V_{pl} and $V_{gs(th)}$ Estimation

As discussed in [Section 2.1](#), the HS MOSFETs carry the inductor current during the PWM on-time and typically incurs most of the switching loss. It is therefore imperative to balance the conduction and switching loss when choosing a high-side MOSFET. [Equation 3](#) shows how to calculate the switching loss. To make accurate predictions in efficiency calculations, accurate switching times for t_r and t_{off} should be determined. Accurate switching times are dependent on the accuracy of Q_{gs} and Q_{gd} as well as $V_{gs(th)}$ and V_{pl} of the MOSFET. These parameters can be found in the MOSFET data sheet.

However the data sheet will specify $V_{gs(th)}$ and V_{pl} values in its characteristic table, the values are only tested with specific drain-source currents. The $V_{gs(th)}$ and V_{pl} will change as drain-source current change. This section will introduce how to estimate the $V_{gs(th)}$ and V_{pl} of a MOSFET by using the output characteristic curves.

[Figure 5](#) shows a typical MOSFETs turn on waveform. The process of MOSFETs turn on can be divided into four stages.

Time between $t_0 - t_1$: time required to bring the gate voltage from zero to $V_{gs(th)}$.

Time between $t_1 - t_2$: the gate voltage has reached $V_{gs(th)}$ and drain current begins to flow.

Time between $t_2 - t_3$: t_2 the drain to source voltage starts to fall. Only C_{Miller} is charged, $V_{gs} = V_{pl}$.

Time between $t_3 - t_4$: gate voltage rises from the plateau up to its final drive voltage, $V_{gs} > V_{pl}$.

[Figure 6](#) shows the output characteristic curves of MOSFET. There are four sections in this curve. The yellow block shows the [Figure 5](#), interval $t_2 - t_3$ is corresponded to the yellow block in [Figure 6](#), the saturation zone of output characteristic curve. In the saturation zone ($v_{gs} > V_{gs(th)}$, $v_{ds} > v_{gs} - V_{gs(th)}$), the MOSFETs satisfied and the drain current can be calculated using [Equation 20](#).

$$i_D = K_n (v_{gs} - V_{gs(th)})^2 \quad (20)$$

i_D is the drain to source current, K_n is the conductance constant, The conductance constant K_n is a physical parameter of MOSFET and is related to the length and width of the channel of the MOSFET, the electron mobility in the inversion layer, and the unit area of the gate (between substrate) oxide.

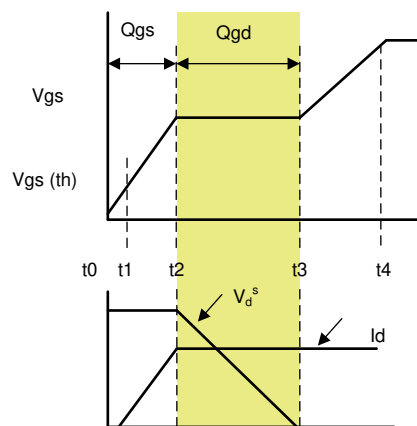


Figure 5. MOSFET Turn on Waveform

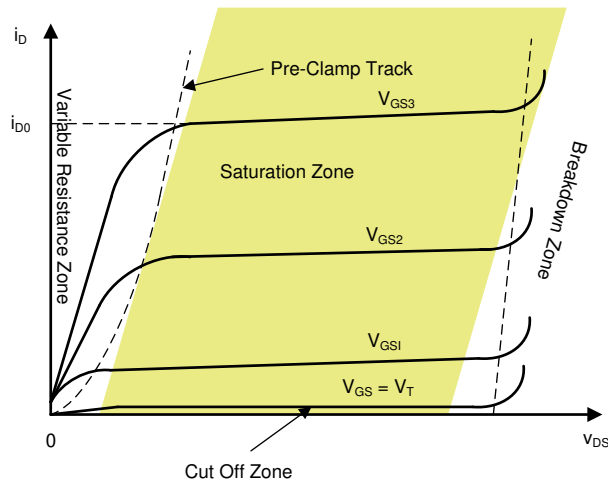


Figure 6. Output Characteristic Curves

Figure 7 is the output characteristic curves given in a MOSFET data sheet. Read from two curves the I_D and V_{gs} and use Equation 21 populating I_{D1} , I_{D2} , V_{gs1} and V_{gs2} to calculate. $V_{gs(th)}$ and K_n can be calculated by using Equation 22 and Equation 23, respectively. Finally the V_{pl} is calculated using Equation 24, populating with the calculated $V_{gs(th)}$ and specified I_{ds} . The V_{pl} is estimated in different drain to source current.

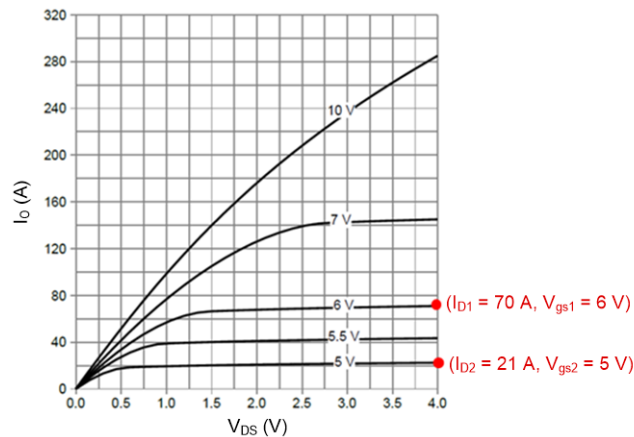


Figure 7. Output Characteristics Curve

$$\begin{cases} i_{D1} = K_n (v_{gs1} - V_{gs(th)})^2 \\ i_{D2} = K_n (v_{gs2} - V_{gs(th)})^2 \end{cases} \quad (21)$$

$$V_{gs(th)} = \frac{v_{gs2} \times \sqrt{\frac{i_{D1}}{i_{D2}}} - v_{gs1}}{\sqrt{\frac{i_{D1}}{i_{D2}}} - 1} \quad (22)$$

$$K_n = \frac{i_{D1}}{(V_{gs1} - V_{gs(th)})^2} \quad (23)$$

$$V_{pl} = \sqrt{\frac{i_D}{K_n}} - V_{gs(th)} \quad (24)$$

According Equation 22 through Equation 24, design the calculator shows in Table 1. We can easily calculate the K_n and $V_{gs(th)}$ by inputting I_d and V_{gs} which obtained from the output characteristic curves of MOSFET data sheet. Using special I_{ds} , we can calculate V_{pl} correspondingly. For example, using MOSFET BSC117N08NS5, $I_{ds} = 10$ A, calculates $V_{pl} = 4.58$ V correspondingly.

Table 1. V_{pl} Calculator

Calculate of $V_{plateau}$		
Input: The Specification from MOSFET data sheet		
V_{gs1}	6	From: Typ. output characteristics (V_{ds} - I_{ds})
$ds1$	70	From: Typ. output characteristics (V_{ds} - I_{ds})
V_{gs2}	5	From: Typ. output characteristics (V_{ds} - I_{ds})
I_{ds2}	21	From: Typ. output characteristics (V_{ds} - I_{ds})
I_{ds}	10	I_{ds} In work condition
The Calculate Output		
K_n	13.51	Conductance constant
V_{gsth}	3.72	Threshold voltage
$V_{plateau}$	4.58	In the condition of I_{ds}

3.2 V_{pl} Calculation Examples

To verify the calculated value for V_{pl} , consider the MOSFETs BSC117N08NS5 and BSC037N08NS5 as examples.

Figure 8 shows the V_{gs} waveforms and resulting V_{pl} for 10 A and 20 A of I_{ds} current using. Table 2 shows the calculated.

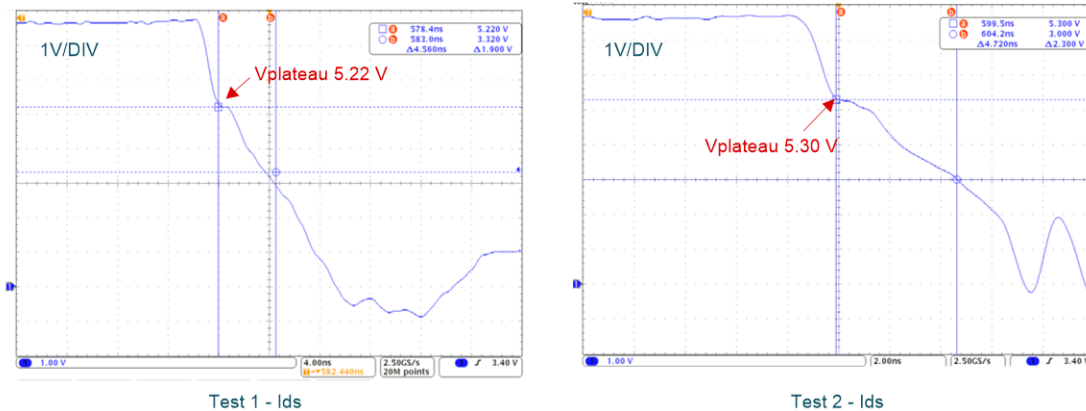


Figure 8. V_{gs} Waveforms of BSC117N08NS5

Table 2. V_{pl} Results Comparison

BSC117N08NS5		
$V_{plateau}$	Test	Calculate (V_{pl})
$I_{ds} = 10$ A	5.22 V	4.58 V
$I_{ds} = 20$ A	5.30 V	4.94 V

Figure 9 show the Vgs waveform of BSC037N08NS5 with drain current 3 A. The waveform shows Vpl = 4.0 V, while the calculated result is 3.91 V.

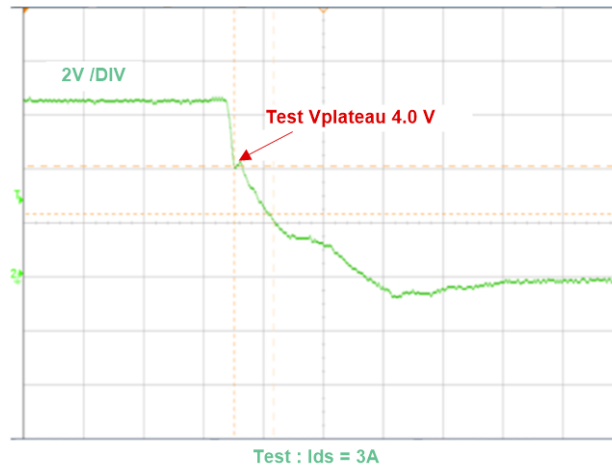


Figure 9. Vgs Waveforms of BSC037N08NS5

From the comparison of these two groups, the test and calculated results are consistent and the errors of them less than 1 V is achieved. As current Id changes, Vpl also changes.

4 Power Losses Calculation and Efficiency Estimation

To verify the accuracy of the calculations for the power loss and to estimate the efficiency, two examples are given in this report. Figure 10 shows the schematic of the LM5145 test board.

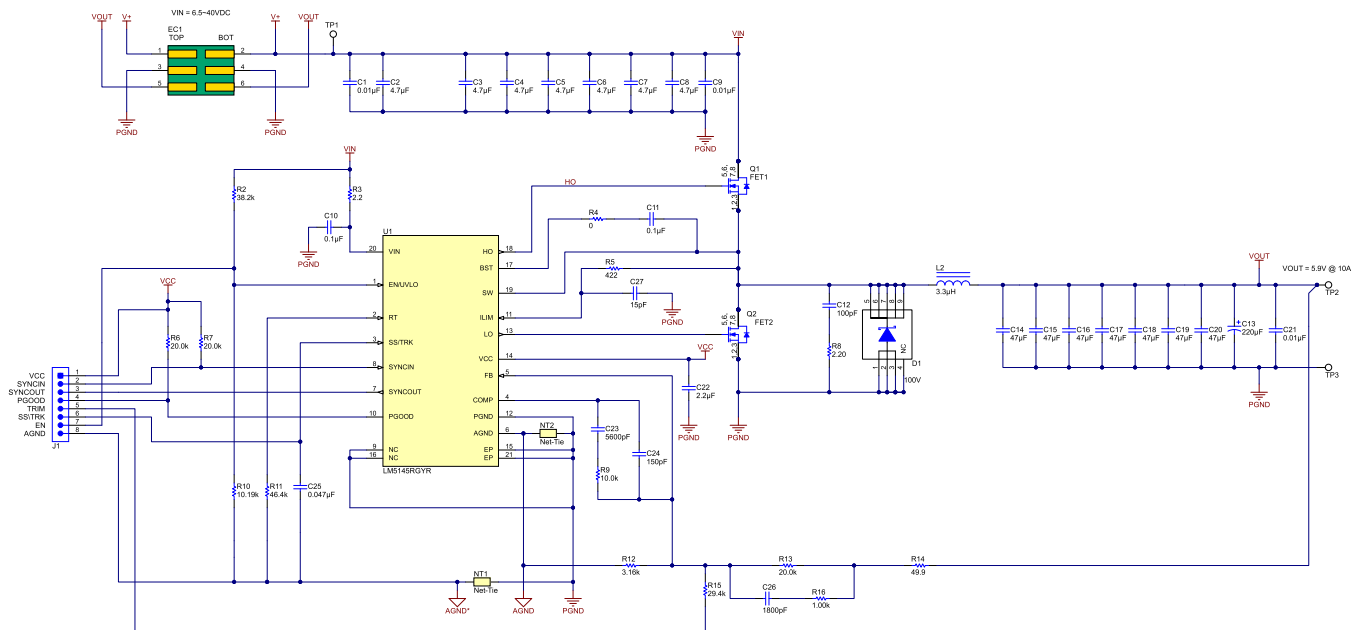


Figure 10. Schematic LM5145

By choosing different HS FET1 switch Q1, there are two group test results.

Table 3. Test Groups

	Q1	Q2
Test condition 1	BSC117N08NS5	BSC037N08NS5
Test condition 2	BSC037N08NS5	BSC037N08NS5

Refer to [Section 3.1](#), the V_{pl} and $V_{gs(th)}$ are 4.58 V and 3.72 V, respectively, for BSC117N08NS5 when the I_{ds} is 10 A. Refer to the [Section 2](#), calculate the power losses step by step. [Table 4](#), [Table 5](#) and [Table 6](#) list the calculated power losses results with different V_{IN} .

Table 4. Power Losses Calculation Results ($V_{IN} = 6.5$ V)

Condition: $V_{IN} = 6.5$ V, $V_{OUT} = 5.9$ V, $I_{OUT} = 10$ A, $f = 230$ kHz, $L = 3.3$ μ H						
	HS-MOSFET	LS-MOSFET	Inductor	Capacitors	Other	Total
Power Loss	2.51 W	0.32 W	0.38 W	0.02 W	0.38 W	3.61 W
Percent	69.5%	8.8%	10.5%	0.6%	10.5%	100%

$V_{IN} = 6.5$ V, the efficiency of calculated is 94.2%, the test efficiency is 94.0%.

Table 5. Power losses Calculation Results ($V_{IN} = 25$ V)

Condition: $V_{IN} = 25$ V, $V_{OUT} = 5.9$ V, $I_{OUT} = 10$ A, $f = 230$ kHz, $L = 3.3$ μ H						
	HS-MOSFET	LS-MOSFET	Inductor	Capacitors	Other	Total
Power Loss	1.07 W	1.16 W	0.98 W	0.03 W	0.17 W	3.41 W
Percent	31.4%	34.0%	28.7%	0.9%	5.0%	100%

$V_{IN} = 25$ V, the efficiency of calculated is 94.5%, the test efficiency is 94.7%.

Table 6. Power Losses Calculation Results ($V_{IN} = 35$ V)

Condition: $V_{IN} = 35$ V, $V_{OUT} = 5.9$ V, $I_{OUT} = 10$ A, $f = 230$ kHz, $L = 3.3$ μ H						
	HS-MOSFET	LS-MOSFET	Inductor	Capacitors	Other	Total
Power Loss	1.05 W	1.38 W	1.13 W	0.03 W	0.19 W	3.78 W
Percent	27.7%	36.5%	29.9%	0.8%	5.0%	100%

$V_{IN} = 35$ V, the efficiency of calculated is 93.9%, the test efficiency is 93.5%.

From [Table 4](#), [Table 5](#) and [Table 6](#), the main power losses of a synchronous buck converter are the switch loss and the inductor loss, which are more than 90%. Besides, with the different V_{IN} , the switch loss and inductor loss also different. The V_{IN} increases, then duty cycle decreases, the switching loss increases and conduction loss decreases. So the HS MOSFETS is in a trade-off between switching loss and conduction loss. The V_{IN} increases, both the LS MOSFET and the inductor losses increase. The inductor losses are as the significant loss in wide V_{IN} applications.

[Figure 11](#), [Figure 12](#) and [Figure 13](#) show the efficiency comparison between estimation and bench test using different input voltages. The curves show efficiency between calculate and test with currents from 5 A to 10 A. From the curves, the efficiency errors are all less than 2%. This shows the accuracy of the calculated of power losses.

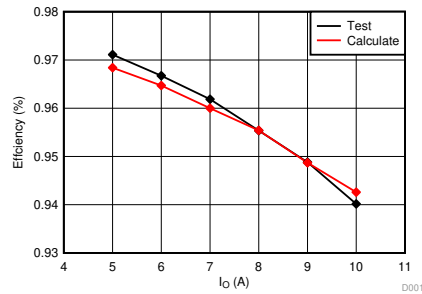


Figure 11. Efficiency Comparison ($V_{IN} = 6.5\text{ V}$)

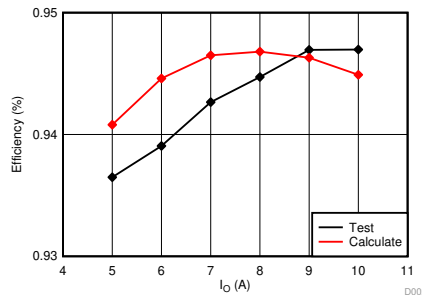


Figure 12. Efficiency Comparison ($V_{IN} = 25\text{ V}$)

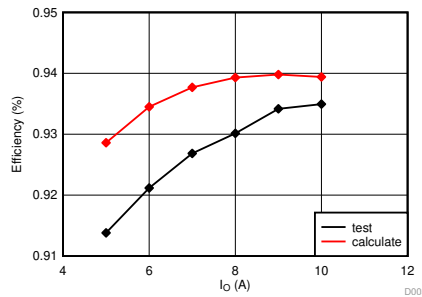


Figure 13. Efficiency Comparison ($V_{IN} = 35\text{ V}$)

In test condition 2, both the HS switch and LS switch Q2 are using BSC037N08NS5.

Figure 14, Figure 15, and Figure 16 show the efficiency comparison between estimation and bench test using different input voltages. The curves show that the efficiency errors between the calculation and test are less than 2%.

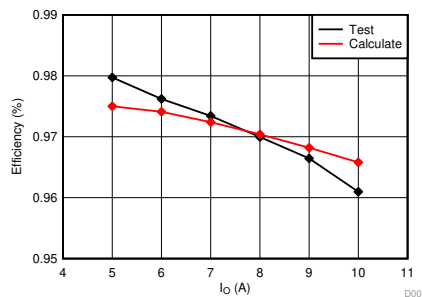
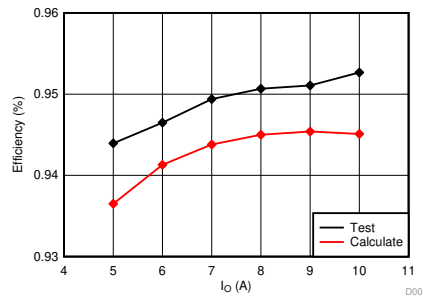
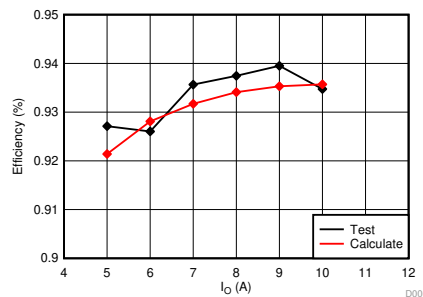


Figure 14. Efficiency Comparison ($V_{IN} = 6.5\text{ V}$)


Figure 15. Efficiency Comparison ($V_{IN} = 25\text{ V}$)

Figure 16. Efficiency Comparison ($V_{IN} = 35\text{ V}$)

5 Summary

This application note summarizes the calculation of the power losses for the synchronous buck converter. The method of evaluating V_{pl} voltage from the output characteristic curve of MOSFET is introduced, which is helpful to improve the accuracy of the switching loss. Finally, it is proved through experiments that the loss estimation method introduced in this paper has improved accuracy in calculating efficiency with the errors being less than 2%. Moreover, the test results show that most of power losses of the synchronous converter come from the switches losses and inductor losses. When the input voltage increases, the losses of the inductor are significant and cannot be ignored.

6 References

1. Texas Instruments, [Power Loss Calculation With Common Source Inductance Consideration for Synchronous Buck Converter Application Report](#)
2. Texas Instruments, [LM5145EVM-HD-20A High Density Evaluation Module User's Guide](#)

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